What is claimed is:

1. A method of forming an electrically active material, comprising:

obtaining a silicon substrate;

forming a first material on said silicon substrate;

forming conductive layer on said first material, said conductive layer formed of a electrically conductive, fully oxidized, transition metal material combined with a SiO2 which is immiscible with said electrically conductive material, and a ferroelectric layer, over said conducting layer;

directly connecting said ferroelectric layer to said other material without a barrier layer therebetween; and

heating said device in high temperature environment between 300 and 700 °C and oxidizing environment without forming substantial oxidization in said material.

2. A method as in claim 1, wherein said material is a dielectric material.

3. A device as in claim 1, wherein said electrical material is formed by sputtering an oxygen containing gas at

least one target containing distinct sites of Ruthenium and silicon.